

## PUBLICATIONS

### Reviewed Journal Publications

1. "Interfacial structures and electrical properties of HfAl<sub>2</sub>O<sub>5</sub> gate dielectric film annealed with a Ti capping layer", X.H. Cheng, L. Wan, Z.R. Song, Y.H. Yu and DaShen Shen, *Appl. Phys Lett*, vol. 90, 152910, 2007
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3. "Characteristics of Hf<sub>x</sub>Si<sub>y</sub>O films grown on Si<sub>0.8</sub>Ge<sub>0.2</sub> layer by electron beam evaporation", X.H. Cheng, Z.R. Song, Y.H. Yu, W.W. Yang, D.S. Shen, *Appl. Phys. Lett*, Vol 88, 122906, 2006.
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6. "Patterned silicon-on-insulator technology for RF Power LDMOSFET", X.H. Cheng, Z.R. Song, Y.M. Dong, Y.H. Yu, D.S. Shen. *Microelectronic Engineering*, Vol. 81(1), p.150-155, 2005
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10. "Electron field emission from SiC/Si heterostructures by high temperature carbon implantation into silicon", Y.M. Xing, J.H. Zhang, W.W. Yang, Y.H. Yu, Z.R. Song, Z.X. Lin and D.S. Shen, *Appl. Phys. Lett*, Vol. 84, p.5461, 2004

11. "Simulation and characterization on properties of AlN films for SOI application", Z.R. Song, Y.H. Yu, S.C. Zou, Z.H. Zheng, D.S. Shen, E.Z. Lou, Z. Xie, B. Sundaravel, S.P. Wong, I.H. Wilson, *Thin Solid Films*, Vol. 459, p.41-47, 2004
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13. "Spectroscopic ellipsometry characterization of the interfacial roughness in SIMOX wafers", W.J. Li, Z.R. Song, K. Tao, X.H. Cheng, W.W. Yang, Y.H. Yu, X. Wang, S.C. Zou, D.S. Shen, *Thin Solid Films*, Vol. 459, p.63-66, 2004
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## Conference Publications

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### **Selected Technical Report**

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